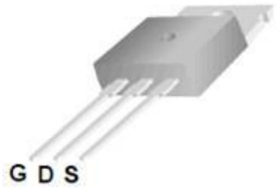
UNIKC
Semiconductor

P1060AT

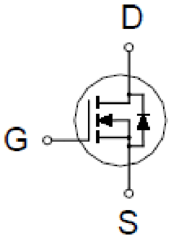
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
600V	0.75Ω @V_{GS} = 10V	10A



TO-220



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	
Continuous Drain Current[2]	T_C = 25 °C	I_D	10	A
	T_C = 100 °C		6	
Pulsed Drain Current[1, 2]		I_{DM}	40	
Avalanche Current[3]		I_{AS}	6.8	
Avalanche Energy[3]	L = 10mH	E_{AS}	236	mJ
Power Dissipation[A]	T_C = 25 °C	P_D	156	W
	T_C = 100 °C		63	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		0.8	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1] Pulse width limited by maximum junction temperature.

[2] Limited only by maximum temperature allowed.

[3] V_{DD} = 60V, starting T_J = 25°C

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250µA	600			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250µA	2.5		4.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±30V			±250	nA
Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600V, V_{GS} = 0V, T_C = 25 °C			25	µA
		V_{DS} = 600V, V_{GS} = 0V , T_C = 100 °C			250	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 5A		0.6	0.75	Ω
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 5A		9.4		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		2120		pF
Output Capacitance	C_{oss}			240		
Reverse Transfer Capacitance	C_{rss}			38		
Total Gate Charge[2]	Q_g	V_{DD} = 300V, V_{GS} = 10V, I_D = 10A		37		nC
Gate-Source Charge[2]	Q_{gs}			10		
Gate-Drain Charge[2]	Q_{gd}			11.7		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 300V, I_D = 10A, R_G = 25Ω		55		nS
Rise Time[2]	t_r			30		
Turn-Off Delay Time[2]	$t_{d(off)}$			210		
Fall Time[2]	t_f			40		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				10	A
Forward Voltage[1]	V_{SD}	I_F = 10A, V_{GS} = 0V			1.5	V
Reverse Recovery Time	t_{rr}	I_F = 10A , dI_F/dt = 100A / µS, V_{GS} = 0V		490		nS
Reverse Recovery Charge	Q_{rr}			4.2		nC

[1] Pulse test : Pulse Width ≤ 300 µsec, Duty Cycle ≤ 2%.

[2] Independent of operating temperature.

[3] Pulse width limited by maximum junction temperature.

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RoHS Compliant

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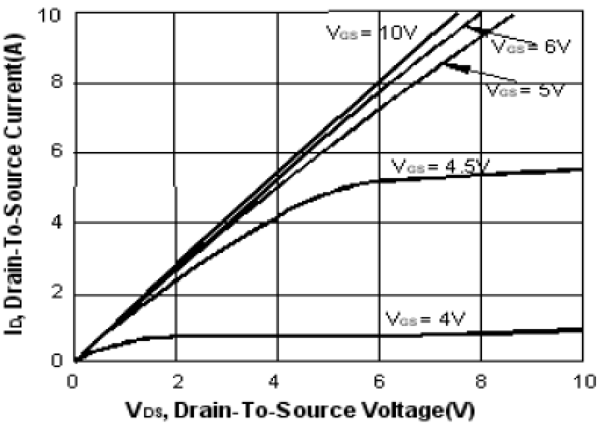
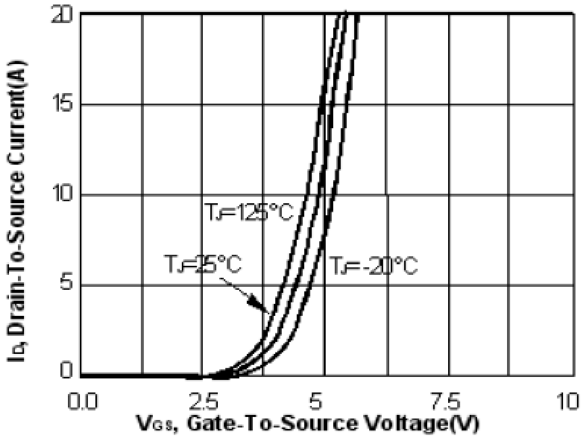
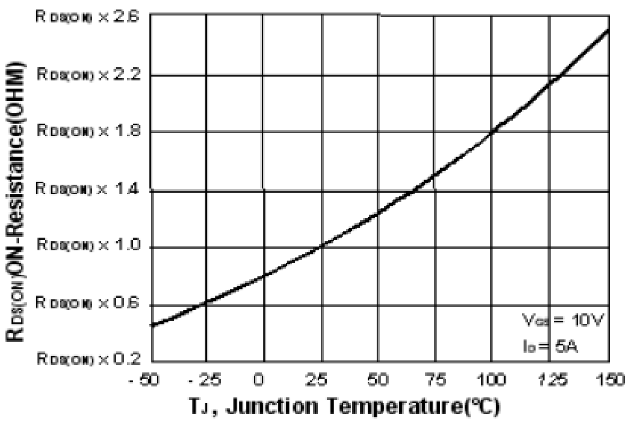
Output Characteristics



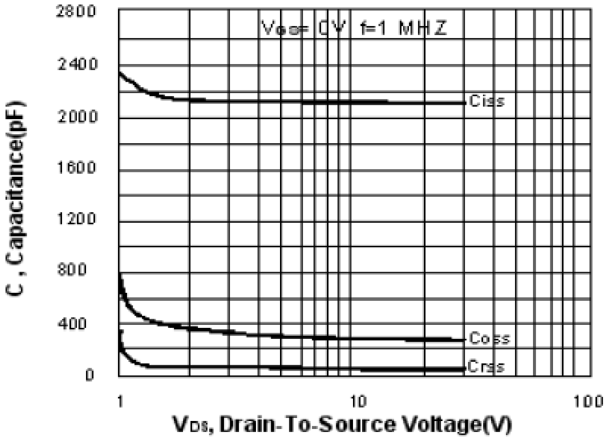
Transfer Characteristics



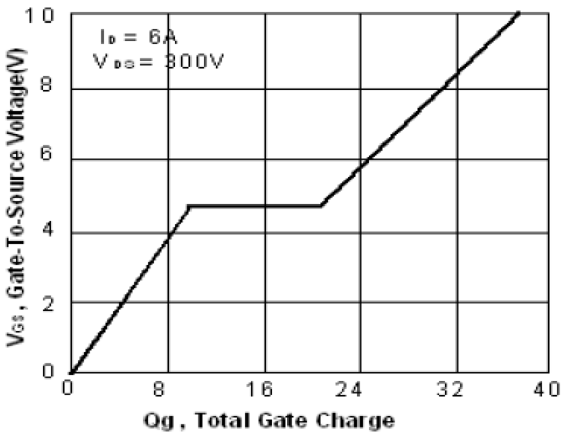
On-Resistance VS Temperature



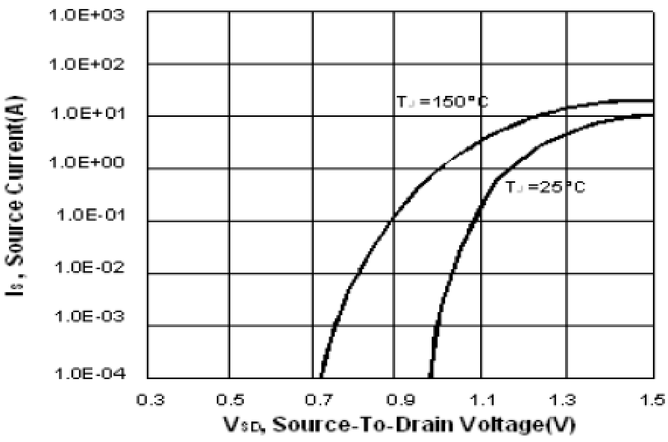
Capacitance Characteristic

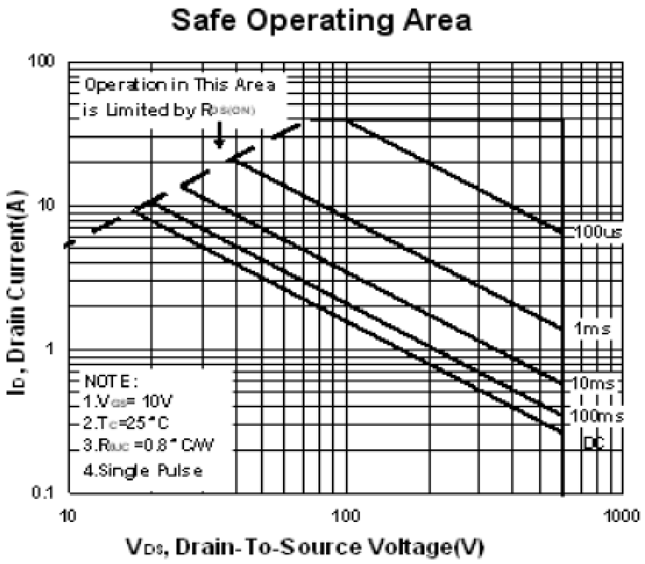


Gate charge Characteristics

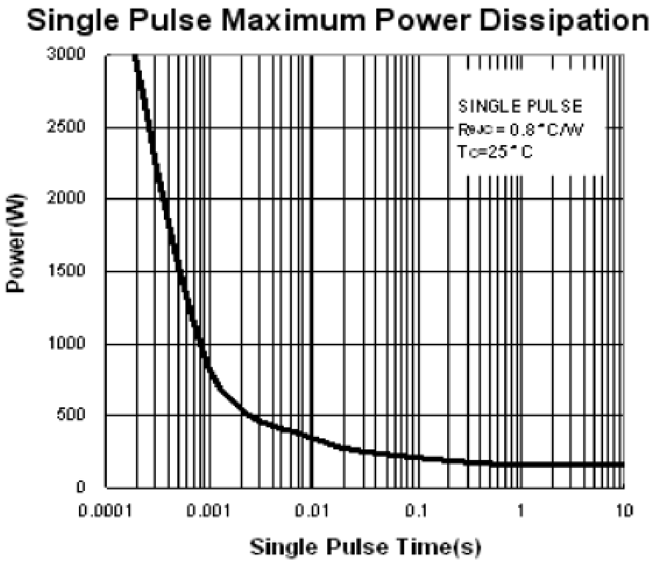


Source-Drain Diode Forward Voltage

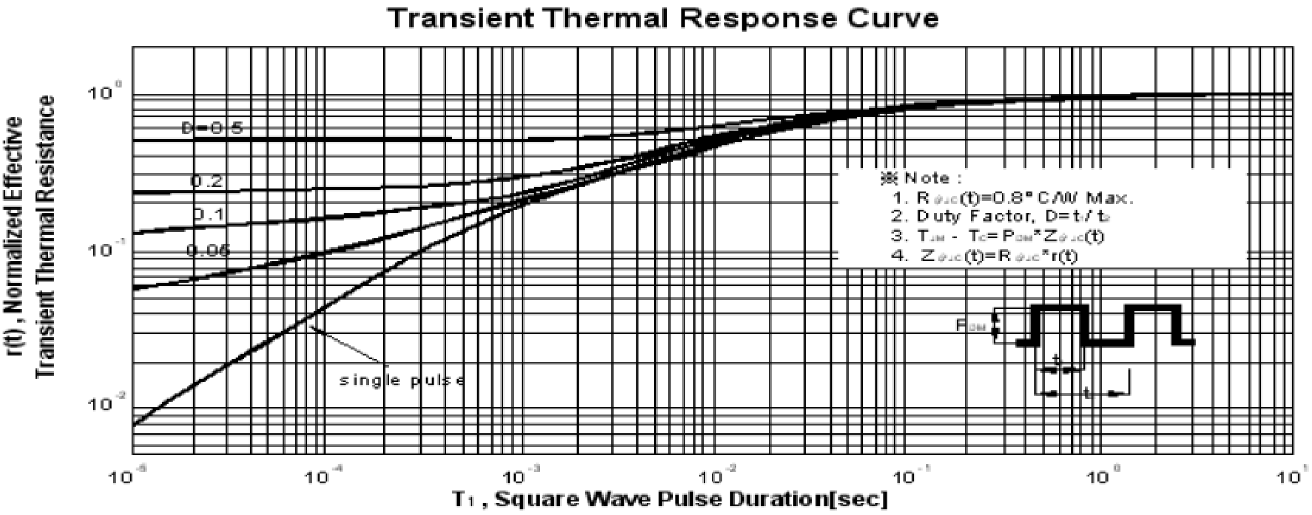




Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

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Package Dimension

TO-220 (3-Lead) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.652	10.16	11.5	H	2.04	2.54	3.04
B	2.54	2.79	3.048	I	1.15	1.52	1.778
C	17.3		22.86	J	3.556	4.57	4.826
D	26.924	29.03	31.242	K	0.508	1.3	1.45
E	14.224	15.45	16.510	L	1.89	2.69	3.09
F	8.382	9.20	9.40	M	0.34	0.5	0.6
G	0.381	0.81	1.016	N